6367254 MOTOROLA SC (XSTRS/R F)

96D 80563 DT-33-11

## MOTOROLA SEMICONDUCTOR TECHNICAL DATA

**BD185 BD187** 

# PLASTIC MEDIUM POWER SILICON NPN TRANSISTOR

. designed for use in 5 to 10 Watt audio amplifiers utilizing complementary or quasi complementary circuits.

- $\bullet$  DC Current Gain—h<sub>FE</sub> = 40 (Min) @ I<sub>C</sub> = 0.5 Adc
- BD 185, 187, 189 are complementary with BD 186, 188, 190

#### MAYIMIM BANGS

Rating	Symbol	Туре	Value	Unit	
Collector-Emitter Voltage	V <sub>CEO</sub>	BD 185 BD 187 BD 189	30 45 60	Vdc Vdc	
Collector-Base Voltage	V <sub>СВО</sub>	BD 185 BD 187 BD 189	40 55 70		
Emitter-Base Voltage	V <sub>EBO</sub>		5	Vdc	
Collector Current	l <sub>C</sub>		4.0	Adc	
Base Current	I <sub>B</sub>		2.0	Adc	
Total Device Dissipation T <sub>C</sub> =25°C Derate above 25°C	, P <sub>D</sub>	40 320		Watts mW/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>		-65 to +150	°C	

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	<sub>θ</sub> јс	3.12	° C/W

### ELECTRICAL CHARACTERISTICS (T<sub>c</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Туре	Min	Max	Unit
Collector-Emitter Sustaining Voltage* (I <sub>C</sub> = 0.1 Adc, I <sub>B</sub> = 0)	BVCEO.	BD 185 BD 187 BD 189	30 45 60		Vdc
Collector Cutoff Current (V <sub>CB</sub> = 40 Vdc,   E = 0) (V <sub>CB</sub> = 55 Vdc,   E = 0) (V <sub>CB</sub> = 70 Vdc,   E = 0)	СВО	BD 185 BD 187 BD 189		0.1 0.1 0.1	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	<sup>I</sup> EBO		-	1.0	mAdc
DC current Gain (I <sub>C</sub> = 0.5 A, V <sub>CE</sub> = 2 V) (I <sub>C</sub> = 2A, V <sub>CE</sub> = 2 V)	h <sub>FE</sub> *		40 15	_	
Collector-Emitter Saturation Voltage* (I <sub>C</sub> = 2Adc, I <sub>B</sub> = 0.2 Adc)	V <sub>CE(sat)</sub>		-	1.0	Vdc
Base-Emitter On Voltage* (I <sub>C</sub> = 2Adc, V <sub>CE</sub> = 2.0 Vdc)	V <sub>BE(on)</sub>		_	1.5	Vdc
Current-Gain-Bandwidth Product (1 <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 MHz)	fτ		2.0		MHz

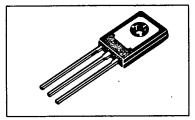
<sup>•</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

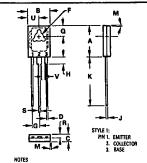
4 AMPERE POWER TRANSISTOR

NPN SILICON

30, 45, 60 VOLTS 40 WATTS

MARCH 1970-E-003





MT = MAIN TERMINAL.
 LEADS, TRUE POSITIONED WITHIN 0.25mm (0.010).
 DIA TO DIM A & 8 AT MAXIMUM MATERIAL CONDITION.

	MELLIMETERS		INCHES		
DM	MEN	MAX	MEN	MAX	
A	10.80	11.04	0.425	0 435	
	7.50	774	0.295	0.305	
0	2 42	2.66	0.095	0.105	
Q	0.51	0 66	0.020	0.026	
F	2.93	3.17	0.115	0.125	
G	2.32	2.46	0 091	0.097	
н	1.27	2.41	0.050	0.095	
1	0.39	063	0015	0.025	
ĸ	14.61	16.63	0.575	0.655	
М.	3° ]	3° TYP		TYP	
P	3.76	4 01	0.148	0 158	
	1 15	1,39	0.045	0.055	
5	064	0.88	0 025	0.035	
ς.	3.69	3.93	0 145	0 155	
٧	1.02	~	0.040	_	

CASE 77-05 TO-126

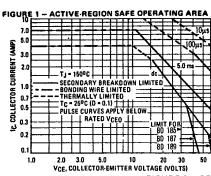


6367254 MOTOROLA SC (XSTRS/R F)

96D 80564 D

BD185, BD187, BD189

T-33-11

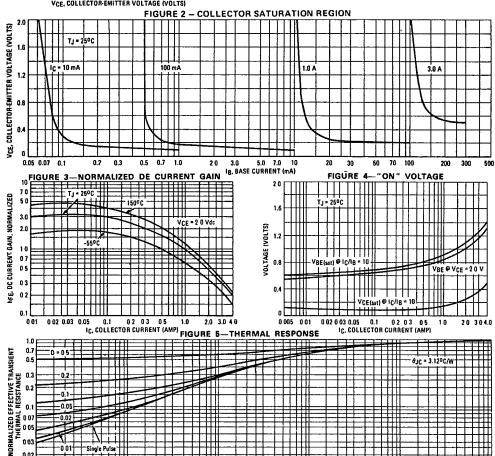


The Safe Operating Area Curves indicate  $I_C-V_{CE}$  limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum  $T_J$ , power-temperature derating must be observed for both steady state and pulse power conditions.

50

200

500 1000





0.01 0.01

0 02 0.03 0 05

0.2 0.3 0.5 2.0 3.0 50